

Toru Ujihara

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

198
papers

2,885
citations

29
h-index

41
g-index

215
ext. papers

3,324
ext. citations

2.2
avg, IF

4.83
L-index

#	Paper	IF	Citations
198	Solvent design aiming at solution property induced surface stability: A case study using SiC solution growth. <i>Journal of Crystal Growth</i> , 2022 , 578, 126425	1.6	1
197	Numerical investigation of solute evaporation in crystal growth from solution: A case study of SiC growth by TSSG method. <i>Journal of Crystal Growth</i> , 2022 , 579, 126448	1.6	0
196	Data-Driven Optimization and Experimental Validation for the Lab-Scale Mono-Like Silicon Ingot Growth by Directional Solidification.. <i>ACS Omega</i> , 2022 , 7, 6665-6673	3.9	2
195	Nucleation sites of expanded stacking faults detected by in operando x-ray topography analysis to design epitaxial layers for bipolar-degradation-free SiC MOSFETs. <i>AIP Advances</i> , 2022 , 12, 035310	1.5	0
194	Kuwahara et al. Reply. <i>Physical Review Letters</i> , 2021 , 127, 229602	7.4	
193	In-operando x-ray topography analysis of SiC metal oxide semiconductor field-effect transistors to visualize stacking fault expansion motions dynamically during operations. <i>Journal of Applied Physics</i> , 2021 , 130, 145703	2.5	3
192	Immobilization of partial dislocations bounding double Shockley stacking faults in 4H-SiC observed by in situ synchrotron X-ray topography. <i>Materialia</i> , 2021 , 20, 101246	3.2	0
191	Chiral Optical Force Generated by a Superchiral Near-Field of a Plasmonic Triangle Trimer as Origin of Giant Bias in Chiral Nucleation: A Simulation Study. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 6209-6221	3.8	3
190	Intensity Interference in a Coherent Spin-Polarized Electron Beam. <i>Physical Review Letters</i> , 2021 , 126, 125501	7.4	6
189	Synchrotron X-ray topographic image contrast variation of screw-type basal plane dislocations located at different depths below the crystal surface in 4H-SiC. <i>Acta Materialia</i> , 2021 , 208, 116746	8.4	4
188	Ordered Arrangement of Planar Faults with Picoscale Perfection in Titanium Oxide Natural Superlattices. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 11175-11181	3.8	2
187	Two-Step Nanoparticle Crystallization via DNA-Guided Self-Assembly and the Nonequilibrium Dehydration Process. <i>Crystal Growth and Design</i> , 2021 , 21, 4506-4515	3.5	1
186	Explainable machine learning for the analysis of transport phenomena in top-seeded solution growth of SiC single crystal. <i>Journal of Thermal Science and Technology</i> , 2021 , 16, JTST0009-JTST0009	0.6	2
185	Geometrical design of a crystal growth system guided by a machine learning algorithm. <i>CrystEngComm</i> , 2021 , 23, 2695-2702	3.3	7
184	Adaptive process control for crystal growth using machine learning for high-speed prediction: application to SiC solution growth. <i>CrystEngComm</i> , 2021 , 23, 1982-1990	3.3	6
183	Temperature dependence of double Shockley stacking fault behavior in nitrogen-doped 4H-SiC studied by in-situ synchrotron X-ray topography. <i>Acta Materialia</i> , 2020 , 194, 387-393	8.4	4
182	Numerical Study of Three-Dimensional Melt Flows during the TSSG Process of SiC Crystal for the Influence of Input Parameters of RF-Coils and an External Rotating Magnetic Field. <i>Crystals</i> , 2020 , 10, 111	2.3	2

181	Effect of Crystal Orientation of Cu Current Collectors on Cycling Stability of Li Metal Anodes. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 9341-9346	9.5	9
180	Design of High-quality SiC Solution Growth Condition Assisted by Machine Learning. <i>Materia Japan</i> , 2020 , 59, 145-152	0.1	
179	Bayesian optimization for a high- and uniform-crystal growth rate in the top-seeded solution growth process of silicon carbide under applied magnetic field and seed rotation. <i>Journal of Crystal Growth</i> , 2020 , 532, 125437	1.6	11
178	Plasmonic Manipulation of Sodium Chlorate Chiral Crystallization: Directed Chirality Transfer via Contact-Induced Polymorphic Transformation and Formation of Liquid Precursor. <i>Crystal Growth and Design</i> , 2020 , 20, 5493-5507	3.5	2
177	Optimal Control of SiC Crystal Growth in the RF-TSSG System Using Reinforcement Learning. <i>Crystals</i> , 2020 , 10, 791	2.3	3
176	Adjoint-based sensitivity analysis for the optimal crucible temperature profile in the RF-Heating TSSG-SiC crystal growth process. <i>Journal of Crystal Growth</i> , 2019 , 517, 59-63	1.6	3
175	In Situ Microscopic Observation on Surface Kinetics in Optical Trapping-Induced Crystal Growth: Step Formation, Wetting Transition, and Nonclassical Growth. <i>Crystal Growth and Design</i> , 2019 , 19, 4138-4150	3.5	2
174	The Effect of Crucible Rotation and Crucible Size in Top-Seeded Solution Growth of Single-Crystal Silicon Carbide. <i>Crystal Research and Technology</i> , 2019 , 54, 1900014	1.3	2
173	The Prediction Model of Crystal Growth Simulation Built by Machine Learning and Its Applications. <i>Vacuum and Surface Science</i> , 2019 , 62, 136-140	0	4
172	Application of C-face dislocation conversion to 2 inch SiC crystal growth on an off-axis seed crystal. <i>CrystEngComm</i> , 2019 , 21, 7260-7265	3.3	6
171	Dislocation Behavior in Bulk Crystals Grown by TSSG Method. <i>Materials Science Forum</i> , 2018 , 924, 39-42	0.4	5
170	Development of angle-resolved spectroscopy system of electrons emitted from a surface with negative electron affinity state. <i>Review of Scientific Instruments</i> , 2018 , 89, 073103	1.7	5
169	Direct observation of stacking fault shrinkage in 4H-SiC at high temperatures by in-situ X-ray topography using monochromatic synchrotron radiation. <i>Applied Physics Letters</i> , 2018 , 113, 012101	3.4	5
168	Suppression of Polytype Transformation with Extremely Low-Dislocation-Density 4H-SiC Crystal in Two-Step Solution Method. <i>Materials Science Forum</i> , 2018 , 924, 60-63	0.4	1
167	Numerical investigation of the effect of static magnetic field on the TSSG growth of SiC. <i>Journal of Crystal Growth</i> , 2018 , 498, 140-147	1.6	10
166	High-speed prediction of computational fluid dynamics simulation in crystal growth. <i>CrystEngComm</i> , 2018 , 20, 6546-6550	3.3	28
165	In Situ Observation of Chiral Symmetry Breaking in NaClO ₃ Chiral Crystallization Realized by Thermoplasmonic Micro-Stirring. <i>Crystal Growth and Design</i> , 2018 , 18, 4230-4239	3.5	4
164	Crystal Orientation Dependence of Precipitate Structure of Electrodeposited Li Metal on Cu Current Collectors. <i>Crystal Growth and Design</i> , 2017 , 17, 2379-2385	3.5	10

163	Global simulation of the induction heating TSSG process of SiC for the effects of Marangoni convection, free surface deformation and seed rotation. <i>Journal of Crystal Growth</i> , 2017 , 470, 75-88	1.6	23
162	Morphology of AlN whiskers grown by reacting N ₂ gas and Al vapor. <i>Journal of Crystal Growth</i> , 2017 , 468, 576-580	1.6	11
161	Numerical investigation of the transport phenomena occurring in the growth of SiC by the induction heating TSSG method. <i>Journal of Crystal Growth</i> , 2017 , 474, 50-54	1.6	15
160	Two-step SiC solution growth for dislocation reduction. <i>Journal of Crystal Growth</i> , 2017 , 468, 874-878	1.6	13
159	Plasmonic Heating-Assisted Laser-Induced Crystallization from a NaClO ₃ Unsaturated Mother Solution. <i>Crystal Growth and Design</i> , 2017 , 17, 809-818	3.5	11
158	Modification of the surface morphology of 4H-SiC by addition of Sn and Al in solution growth with SiCr solvents. <i>Journal of Crystal Growth</i> , 2017 , 458, 37-43	1.6	14
157	Phase transition process in DDAB supported lipid bilayer. <i>Journal of Crystal Growth</i> , 2017 , 468, 88-92	1.6	1
156	Temperature dependence of carrier relaxation time in gallium phosphide evaluated by photoemission measurements. <i>AIP Advances</i> , 2017 , 7, 115314	1.5	3
155	Coherence of a pulsed electron beam extracted from a semiconductor photocathode in transmission electron microscope 2016 , 318-319		0
154	Characterization of V-Shaped Defects Formed during the 4H-SiC Solution Growth by Transmission Electron Microscopy and X-ray Topography Analysis. <i>Crystal Growth and Design</i> , 2016 , 16, 5136-5140	3.5	3
153	Spatial Distribution of Carrier Concentration in 4H-SiC Crystal Grown by Solution Method. <i>Materials Science Forum</i> , 2016 , 858, 57-60	0.4	1
152	Polytype control by activity ratio of silicon to carbon during SiC solution growth using multicomponent solvents. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 01AC01	1.4	0
151	Conversion Behavior of Threading Screw Dislocations on C Face with Different Surface Morphology During 4H-SiC Solution Growth. <i>Crystal Growth and Design</i> , 2016 , 16, 6436-6439	3.5	14
150	Septin Interferes with the Temperature-Dependent Domain Formation and Disappearance of Lipid Bilayer Membranes. <i>Langmuir</i> , 2016 , 32, 12823-12832	4	9
149	Effect of magnesium ion concentration on two-dimensional structure of DNA-functionalized nanoparticles on supported lipid bilayer. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 03DF11	1.4	8
148	Thin film growth of CaFe ₂ As ₂ by molecular beam epitaxy. <i>Superconductor Science and Technology</i> , 2016 , 29, 015013	3.1	7
147	The Boersch effect in a picosecond pulsed electron beam emitted from a semiconductor photocathode. <i>Applied Physics Letters</i> , 2016 , 109, 013108	3.4	17
146	Analysis of the carbon transport near the growth interface with respect to the rotational speed of the seed crystal during top-seeded solution growth of SiC. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 125601	1.4	10

145	Enantioselective amplification on circularly polarized laser-induced chiral nucleation from a NaClO ₃ solution containing Ag nanoparticles. <i>CrystEngComm</i> , 2016 , 18, 7441-7448	3.3	18
144	Dislocation Conversion During SiC Solution Growth for High-Quality Crystals. <i>Materials Science Forum</i> , 2015 , 821-823, 3-8	0.4	11
143	4H-SiC Growth from Si-Cr-C Solution under Al and N Co-Doping Conditions. <i>Materials Science Forum</i> , 2015 , 821-823, 9-13	0.4	10
142	Effect of aluminum addition on the surface step morphology of 4H-SiC grown from Si ₃ N ₄ solution. <i>Journal of Crystal Growth</i> , 2015 , 423, 45-49	1.6	33
141	Non-uniform electrodeposition of zinc on the (0001) plane. <i>Thin Solid Films</i> , 2015 , 590, 207-213	2.2	16
140	Change in Surface Morphology by Addition of Impurity Elements in 4H-SiC Solution Growth with Si Solvent. <i>Materials Science Forum</i> , 2015 , 821-823, 14-17	0.4	5
139	Control of Interface Shape by Non-Axisymmetric Solution Convection in Top-Seeded Solution Growth of SiC Crystal. <i>Materials Science Forum</i> , 2015 , 821-823, 18-21	0.4	3
138	3C-SiC Crystal on Sapphire by Solution Growth Method. <i>Materials Science Forum</i> , 2015 , 821-823, 185-188	0.4	3
137	Effect of Forced Convection by Crucible Design in Solution Growth of SiC Single Crystal. <i>Materials Science Forum</i> , 2015 , 821-823, 22-25	0.4	3
136	Improvement of Surface Morphology by Solution Flow Control in Solution Growth of SiC on Off-Axis Seeds. <i>Materials Science Forum</i> , 2015 , 821-823, 31-34	0.4	6
135	Influences of Solution Flow and Lateral Temperature Distribution on Surface Morphology in Solution Growth of SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 35-38	0.4	1
134	Research on Solvent Composition for Different Surface Morphology on C Face during 4H-SiC Solution Growth. <i>Materials Science Forum</i> , 2015 , 821-823, 39-42	0.4	3
133	Coherences of spin-polarized and pulsed electron beam extracted from a semiconductor photocathode in TEM. <i>Microscopy (Oxford, England)</i> , 2015 , 64, i17.1-i17	1.3	3
132	The strain effect on the superconducting properties of BaFe ₂ (As, P) ₂ thin films grown by molecular beam epitaxy. <i>Superconductor Science and Technology</i> , 2014 , 27, 065005	3.1	25
131	Low-dislocation-density 4H-SiC crystal growth utilizing dislocation conversion during solution method. <i>Applied Physics Express</i> , 2014 , 7, 065501	2.4	34
130	Emergence and Amplification of Chirality via Achiral-Chiral Polymorphic Transformation in Sodium Chlorate Solution Growth. <i>Crystal Growth and Design</i> , 2014 , 14, 3596-3602	3.5	12
129	Top-seeded solution growth of three-inch-diameter 4H-SiC using convection control technique. <i>Journal of Crystal Growth</i> , 2014 , 395, 68-73	1.6	45
128	Different behavior of threading edge dislocation conversion during the solution growth of 4H-SiC depending on the Burgers vector. <i>Acta Materialia</i> , 2014 , 81, 284-290	8.4	22

127	Solubility measurement of a metastable achiral crystal of sodium chlorate in solution growth. <i>Journal of Crystal Growth</i> , 2014 , 394, 106-111	1.6	11
126	Forming two-dimensional structure of DNA-functionalized Au nanoparticles via lipid diffusion in supported lipid bilayers. <i>Journal of Crystal Growth</i> , 2014 , 401, 494-498	1.6	11
125	Nitrogen doping of 4H-SiC by the top-seeded solution growth technique using Si ₃ N ₄ solvent. <i>Journal of Crystal Growth</i> , 2014 , 392, 60-65	1.6	29
124	Coherence of a spin-polarized electron beam emitted from a semiconductor photocathode in a transmission electron microscope. <i>Applied Physics Letters</i> , 2014 , 105, 193101	3.4	29
123	Growth of a smooth CaF ₂ layer on NdFeAsO thin film. <i>Journal of Physics: Conference Series</i> , 2014 , 507, 012047	0.3	3
122	Increase in the Growth Rate by Rotating the Seed Crystal at High Speed during the Solution Growth of SiC. <i>Materials Science Forum</i> , 2014 , 778-780, 63-66	0.4	9
121	Surface Morphology and Threading Dislocation Conversion Behavior during Solution Growth of 4H-SiC Using Al-Si Solvent. <i>Materials Science Forum</i> , 2014 , 778-780, 67-70	0.4	13
120	Top-Seeded Solution Growth of 3 Inch Diameter 4H-SiC Bulk Crystal Using Metal Solvents. <i>Materials Science Forum</i> , 2014 , 778-780, 79-82	0.4	10
119	Growth rate and surface morphology of 4H-SiC crystals grown from Si ₃ N ₄ and Si ₃ N ₄ /Al ₂ O ₃ solutions under various temperature gradient conditions. <i>Journal of Crystal Growth</i> , 2014 , 401, 681-685	1.6	50
118	Influence of Solution Flow on Step Bunching in Solution Growth of SiC Crystals. <i>Crystal Growth and Design</i> , 2013 , 13, 3691-3696	3.5	28
117	Effect of Surface Polarity on the Conversion of Threading Dislocations in Solution Growth. <i>Materials Science Forum</i> , 2013 , 740-742, 15-18	0.4	8
116	Achiral Metastable Crystals of Sodium Chlorate Forming Prior to Chiral Crystals in Solution Growth. <i>Crystal Growth and Design</i> , 2013 , 13, 5188-5192	3.5	15
115	Critical current density and grain boundary property of BaFe ₂ (As,P) ₂ thin films. <i>Physica C: Superconductivity and Its Applications</i> , 2013 , 494, 181-184	1.3	35
114	Phase-locking of oscillating images using laser-induced spin-polarized pulse TEM. <i>Microscopy (Oxford, England)</i> , 2013 , 62, 607-14	1.3	4
113	Bulk 3C-SiC Crystal by Top Seeded Solution Growth Method. <i>Materials Science Forum</i> , 2013 , 740-742, 311-314	0.4	5
112	Reduction of Threading Screw Dislocation Utilizing Defect Conversion during Solution Growth of 4H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 189-192	0.4	15
111	Evolution of threading screw dislocation conversion during solution growth of 4H-SiC. <i>APL Materials</i> , 2013 , 1, 022109	5.7	34
110	Direct Growth of AlN Single Crystal on Sapphire by Solution Growth Method. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JE17	1.4	6

109	Substrate dependence of the superconducting properties of NdFeAs(O,F) thin films. <i>Solid State Communications</i> , 2012 , 152, 735-739	1.6	24
108	Polytype Transformation by Replication of Stacking Faults Formed by Two-Dimensional Nucleation on Spiral Steps during SiC Solution Growth. <i>Crystal Growth and Design</i> , 2012 , 12, 3209-3214	3.5	26
107	Polytype-selective growth of SiC by supersaturation control in solution growth. <i>Journal of Crystal Growth</i> , 2012 , 360, 176-180	1.6	18
106	Analysis of thickness modulation in GaAs/GaAsP strained superlattice by TEM observation. <i>Journal of Crystal Growth</i> , 2012 , 353, 84-87	1.6	3
105	Stable Growth of 4H-SiC Single Polytype by Controlling the Surface Morphology Using a Temperature Gradient in Solution Growth. <i>Materials Science Forum</i> , 2012 , 717-720, 53-56	0.4	5
104	Conversion Mechanism of Threading Screw Dislocation during SiC Solution Growth. <i>Materials Science Forum</i> , 2012 , 717-720, 351-354	0.4	29
103	30-kV spin-polarized transmission electron microscope with GaAs/GaAsP strained superlattice photocathode. <i>Applied Physics Letters</i> , 2012 , 101, 033102	3.4	44
102	High-Efficiency Conversion of Threading Screw Dislocations in 4H-SiC by Solution Growth. <i>Applied Physics Express</i> , 2012 , 5, 115501	2.4	54
101	Development of Spin-Polarized Pulsed TEM. <i>Journal of Physics: Conference Series</i> , 2012 , 371, 012004	0.3	2
100	Polytype Stability of 4H-SiC Seed Crystal on Solution Growth. <i>Materials Science Forum</i> , 2011 , 679-680, 24-27	0.4	3
99	Formation process of 3C-SiC on 6H-SiC (0001) by low-temperature solution growth in SiBCl system. <i>Journal of Crystal Growth</i> , 2011 , 335, 94-99	1.6	15
98	Molecular Beam Epitaxy Growth of Superconducting NdFeAs(O,F) Thin Films Using a F-Getter and a Novel F-Doping Method. <i>Applied Physics Express</i> , 2011 , 4, 083102	2.4	31
97	Epitaxial growth of LaFeAs(O,F) thin films by molecular beam epitaxy. <i>Physica C: Superconductivity and Its Applications</i> , 2011 , 471, 1174-1176	1.3	6
96	Anomalous diffusion in supported lipid bilayers induced by oxide surface nanostructures. <i>Langmuir</i> , 2011 , 27, 9662-5	4	28
95	Increase of spectral width of stacked InAs quantum dots on GaAs by controlling spacer layer thickness. <i>Journal of Crystal Growth</i> , 2011 , 318, 1113-1116	1.6	
94	High-quality and large-area 3CBiC growth on 6HBiC(0 0 0 1) seed crystal with top-seeded solution method. <i>Journal of Crystal Growth</i> , 2011 , 318, 389-393	1.6	16
93	Defect Evaluation of SiC Crystal Grown by Solution Method: The Study by Synchrotron X-Ray Topography and Etching Method. <i>Materials Science Forum</i> , 2011 , 679-680, 28-31	0.4	5
92	Stacking Faults around the Hetero-Interface Induced by 6H-SiC Polytype Transformation on 3C-SiC with Solution Growth. <i>Materials Science Forum</i> , 2010 , 645-648, 363-366	0.4	1

91	Real Time Magnetic Imaging by Spin-Polarized Low Energy Electron Microscopy with Highly Spin-Polarized and High Brightness Electron Gun. <i>Applied Physics Express</i> , 2010 , 3, 026601	2.4	35
90	In situ growth of superconducting NdFeAs(O,F) thin films by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 042509	3.4	55
89	Effects of defects and local thickness modulation on spin-polarization in photocathodes based on GaAs/GaAsP strained superlattices. <i>Journal of Applied Physics</i> , 2010 , 108, 094509	2.5	11
88	Strain of GaAs/GaAsP Superlattices Used as Spin-Polarized Electron Photocathodes, Determined by X-Ray Diffraction. <i>E-Journal of Surface Science and Nanotechnology</i> , 2010 , 8, 125-130	0.7	1
87	Study of minority carrier diffusion length in multicrystalline silicon solar cells using photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2009 , 95, 191908	3.4	16
86	Anisotropy of mosaic structure of GaAsP layers grown on GaAs substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1785-1789	1.6	1
85	Polytype and Crystal Quality of SiC Crystals Grown on 3C-SiC by Seeded Solution Method. <i>Materials Science Forum</i> , 2009 , 615-617, 27-30	0.4	3
84	Effects of Applied Voltage on the Size of Phase-Separated Domains in DMPS-DOPC Lipid Binary Bilayers Supported on SiO ₂ /Si Substrates. <i>Transactions of the Materials Research Society of Japan</i> , 2009 , 34, 217-220	0.2	
83	Local Condensation of Artificial Raft Domains under Light Irradiation in Supported Lipid Bilayer of PSM-DOPC-Cholesterol System. <i>Transactions of the Materials Research Society of Japan</i> , 2009 , 34, 179-182 ^{0.2}		
82	Shape Transformation of Adsorbed Vesicles on Oxide Surfaces: Effect of Substrate Material and Photo-Irradiation. <i>Transactions of the Materials Research Society of Japan</i> , 2009 , 34, 183-188	0.2	3
81	Epitaxial Growth of NdFeAsO Thin Films by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2009 , 2, 093002	2.4	50
80	Solution Growth of SiC Crystals in Si-Ti and Si-Ge-Ti Solvents. <i>Materials Science Forum</i> , 2008 , 600-603, 59-62	0.4	4
79	Lipid bilayer membrane with atomic step structure: supported bilayer on a step-and-terrace TiO ₂ (100) surface. <i>Langmuir</i> , 2008 , 24, 11567-76	4	70
78	Local concentration of gel phase domains in supported lipid bilayers under light irradiation in binary mixture of phospholipids doped with dyes for photoinduced activation. <i>Langmuir</i> , 2008 , 24, 10974-80	4.80	10
77	Super-High Brightness and High-Spin-Polarization Photocathode. <i>Applied Physics Express</i> , 2008 , 1, 045002.4	2.4	57
76	Stability Growth Condition for 3C-SiC Crystals by Solution Technique. <i>Materials Science Forum</i> , 2008 , 600-603, 63-66	0.4	3
75	High brightness and high polarization electron source using transmission photocathode with GaAs-GaAsP superlattice layers. <i>Journal of Applied Physics</i> , 2008 , 103, 064905	2.5	45
74	Minority carrier lifetime in polycrystalline silicon solar cells studied by photoassisted Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2008 , 93, 021902	3.4	53

73	2P-229 In situ Observation of Molecular Diffusion in Supported Lipid Bilayer on Oxide Surfaces by Substrate-Derestricted Single-Molecule Tracking(The 46th Annual Meeting of the Biophysical Society of Japan). <i>Seibutsu Butsuri</i> , 2008 , 48, S110	0	
72	Effects of absorbed group-V atoms on the size distribution and optical properties of InAsP quantum dots fabricated by the droplet hetero-epitaxy. <i>Journal of Crystal Growth</i> , 2008 , 310, 2239-2243	1.6	6
71	Solution growth of high-quality 3C-SiC crystals. <i>Journal of Crystal Growth</i> , 2008 , 310, 1438-1442	1.6	25
70	Highly spin-polarized electron photocathode based on GaAs δ GaAsP superlattice grown on mosaic-structured buffer layer. <i>Journal of Crystal Growth</i> , 2008 , 310, 5039-5043	1.6	22
69	Effect of Li doping on photoluminescence from Er, O-codoped GaAs. <i>Journal of Crystal Growth</i> , 2007 , 298, 69-72	1.6	11
68	Photovoltage Mapping on Polycrystalline Silicon Solar Cells by Kelvin Probe Force Microscopy with Piezoresistive Cantilever. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 5548-5551	1.4	30
67	Thermal emittance measurements for electron beams produced from bulk and superlattice negative electron affinity photocathodes. <i>Journal of Applied Physics</i> , 2007 , 102, 024904	2.5	31
66	Supported lipid bilayer membranes on SiO ₂ and TiO ₂ : substrate effects on membrane formation and shape transformation 2007 ,		8
65	Photovoltage Mapping on Polycrystalline Silicon Solar Cells through Potential Measurements by Atomic Force Microscopy with Piezoresistive Cantilever. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2128-2131	1.4	14
64	Solution Growth of SiC Crystal with High Growth Rate Using Accelerated Crucible Rotation Technique. <i>Materials Science Forum</i> , 2006 , 527-529, 119-122	0.4	36
63	Size uniformity of InAs dots on mesa-structure templates on (001) InP substrates grown by droplet metal-organic vapor phase epitaxy method. <i>Applied Physics Letters</i> , 2006 , 89, 083110	3.4	9
62	Growth of SiC Single Crystal from Si-C-(Co, Fe) Ternary Solution. <i>Materials Science Forum</i> , 2006 , 527-529, 115-118	0.4	3
61	2P293 Formation of domains in fluorescent lipids doped DMPC-DOPC binary bilayers supported on SiO ₂ /Si substrates under local light irradiation.(40. Membrane structure,Poster Session,Abstract,Meeting Program of EABS & BSJ 2006). <i>Seibutsu Butsuri</i> , 2006 , 46, S369	0	
60	Pattern size effect on source supply process for sub-micrometer scale selective area growth by organometallic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2006 , 289, 89-95	1.6	12
59	Growth of InGaAs and SiGe homogeneous bulk crystals which have complete miscibility in the phase diagrams. <i>International Journal of Materials and Product Technology</i> , 2005 , 22, 185	1	5
58	Effects of vicinal steps on the island growth and orientation of epitaxially grown perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) thin film crystals on a hydrogen-terminated Si(1 1 1) substrate. <i>Journal of Crystal Growth</i> , 2005 , 273, 594-602	1.6	9
57	Growth of SiGe-on-insulator and its application as a substrate for epitaxy of strained-Si layer. <i>Journal of Crystal Growth</i> , 2005 , 275, e1203-e1207	1.6	3
56	A simple approach to determine preferential growth orientation using multiple seed crystals with random orientations and its utilization for seed optimization to restrain polycrystallization of SiGe bulk crystal. <i>Journal of Crystal Growth</i> , 2005 , 276, 393-400	1.6	15

55	Structural properties of directionally grown polycrystalline SiGe for solar cells. <i>Journal of Crystal Growth</i> , 2005 , 275, 467-473	1.6	13
54	Crystal quality of a 6H-SiC layer grown over macrodefects by liquid-phase epitaxy: a Raman spectroscopic study. <i>Thin Solid Films</i> , 2005 , 476, 206-209	2.2	23
53	Influence of growth temperature on minority-carrier lifetime of Si layer grown by liquid phase epitaxy using Ga solvent. <i>Journal of Applied Physics</i> , 2005 , 98, 073708	2.5	1
52	Crystalline Quality Evaluation of 6H-SiC Bulk Crystals Grown from Si-Ti-C Ternary Solution. <i>Materials Science Forum</i> , 2005 , 483-485, 13-16	0.4	21
51	Ge composition dependence of properties of solar cells based on multicrystalline SiGe with microscopic compositional distribution. <i>Journal of Applied Physics</i> , 2004 , 96, 1238-1241	2.5	28
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